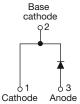
**Vishay Semiconductors** 

# HEXFRED<sup>®</sup> Ultrafast Soft Recovery Diode, 4 A



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PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub> 4 A					
V <sub>R</sub>	600 V				
V <sub>F</sub> at I <sub>F</sub>	1.4 V				
t <sub>rr</sub> typ.	17 ns				
T <sub>J</sub> max.	150 °C				
Package	2L TO-220AC				
Circuit configuration	Single				

### FEATURES

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47



 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

### DESCRIPTION

VS-HFA04TB60 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the VS-HFA04TB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA04TB60 ... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V <sub>R</sub>		600	V		
Maximum continuous forward current	١ <sub>F</sub>	T <sub>C</sub> = 100 °C	4			
Single pulse forward current	I <sub>FSM</sub>		25	А		
Maximum repetitive forward current	I <sub>FRM</sub>		16			
Maximum power dissipation	PD	T <sub>C</sub> = 25 °C	25	W		
Maximum power dissipation		T <sub>C</sub> = 100 °C	10	~~~		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C		

Revision: 23-Nov-17

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ELECTRICAL SPECIFICATIONS (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		600	-	-		
	I <sub>F</sub> = 4.0 A			-	1.5	1.8	V	
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 8.0 A	See fig. 1	-	1.8	2.2		
		I <sub>F</sub> = 4.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7		
Maximum reverse		$V_{R} = V_{R}$ rated	See fig. 2	-	0.17	3.0		
leakage current	I <sub>RM</sub>	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See lig. 2	-	44	300	μA	
Junction capacitance	CT	V <sub>R</sub> = 200 V	See fig. 3	-	4.0	8.0	pF	
Series inductance	Ls	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH	

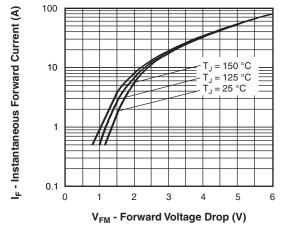
<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t <sub>rr</sub>	$I_F = 1.0 \text{ A},  dI_F/dt = 200$	A/μs, V <sub>R</sub> = 30 V	-	17	-			
Reverse recovery time See fig. 5, 6 and 16	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	28	42	ns		
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	38	57			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 4 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	2.9	5.2	А		
See fig. 7 and 8	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	3.7	6.7	A		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	40	60	nC		
See fig. 9 and 10	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	70	105			
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 11 and 12	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	280	-			
	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	235	-	A/µs		

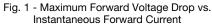
THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	5.0		
Thermal resistance, junction to ambient	R <sub>thA</sub>	Typical socket mount	-	-	80	K/W	
Thermal resistance, case to heatsink	R <sub>thS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-		
Weight			-	2.0	-	g	
weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style 2L TO-220AC		HFA0	4TB60		



# VS-HFA04TB60-M3

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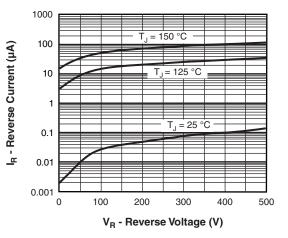


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

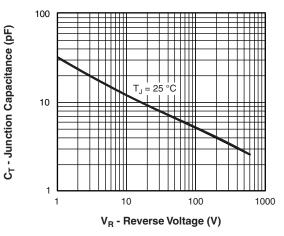


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

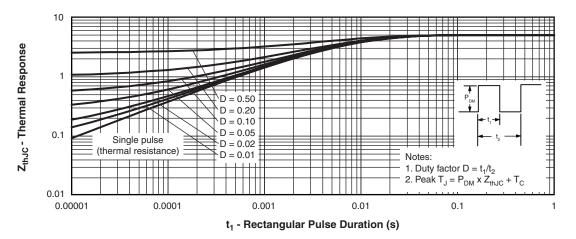
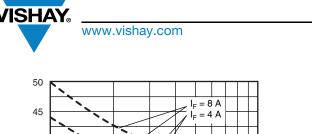
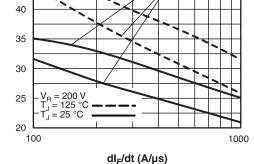


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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t<sub>rr</sub> (ns)

Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

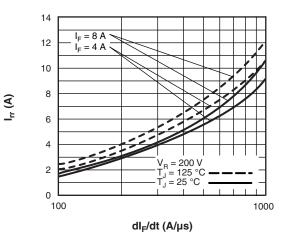


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt



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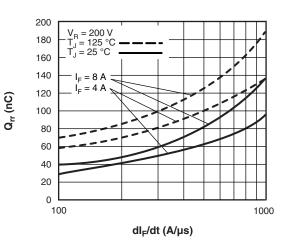


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

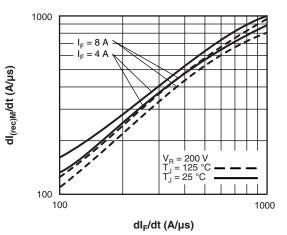


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt

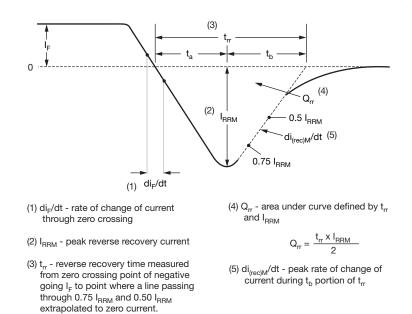


Fig. 9 - Reverse Recovery Waveform and Definitions

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## Vishay Semiconductors



### **ORDERING INFORMATION TABLE**

Device code	VS-	HF	Α	04	тв	60	-M3
	1	2	3	4	5	6	7
			nay Sem KFRED <sup>®</sup>		ctors pr	oduct	
	3.	Elec	ctron irra rent rati	adiated	= 4 A)		
	5	- Pac	kage: = 2L TC	0	,		
	6 7	- Vol	tage rati ironmer	ng (60 =	= 600 V)		
			s = halog	•		-compli	ant, and

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-HFA04TB60-M3	50	1000	Antistatic plastic tube			

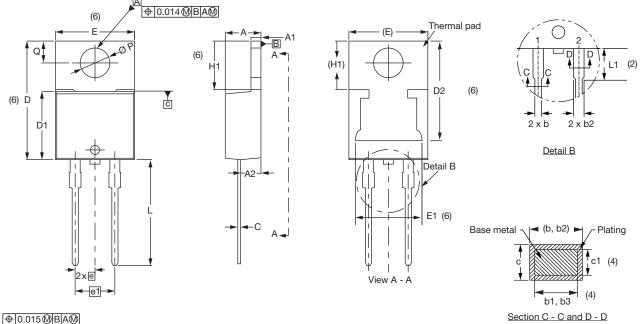
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96156			
Part marking information	www.vishay.com/doc?95391			

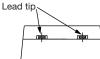


**Vishay Semiconductors** 

# 2L TO-220AC

### **DIMENSIONS** in millimeters and inches





SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	AX. MIN.		NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

Conforms to JEDEC®	outline	TO-220AC
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SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

#### Notes

 $^{(1)}\,$  Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

<sup>(3)</sup> Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

<sup>(4)</sup> Dimension b1, b3, and c1 apply to base metal only

(5) Controlling dimensions: inches

<sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2, and E1

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> TO-220, except D2

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 NTE5990
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